

# FQPF18N60C

## 18A 600V N-Channel MOSFET



Symbol	Parameter	FQPF18N60C	Unit
$V_{DSS}$	Drain-Source Voltage	600	V
$I_D$	- Continuous ( $T_C = 25^\circ\text{C}$ )	18	A
	- Continuous ( $T_C = 100^\circ\text{C}$ )	11.4*	
$I_{DM}$	Drain Current - Pulsed (Note 1)	72	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	1305	mJ
$I_{AR}$	Avalanche Current (Note 1)	12	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	22.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
$P_D$	Power Dissipation	51	W
	- $T_C = 25^\circ\text{C}$ )	0.41	W/°C
	- Derate above $25^\circ\text{C}$		
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	°C
$T_L$	Maximum Lead Temperature for Soldering Purpose, $1/8^\circ$ from case for 5 seconds	300	°C

\* Drain current limited by maximum junction temperature